

EXPRESS MAIL LABEL NO.: EL814454825US

PROCESS FOR FABRICATING A SINGLE-CRYSTAL SUBSTRATE AND
INTEGRATED CIRCUIT COMPRISING SUCH A SUBSTRATE

ABSTRACT OF THE DISCLOSURE

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An initial single-crystal substrate 1 having, locally and on the surface, at least one discontinuity in the single-crystal lattice is formed. The initial substrate is recessed at the discontinuity. The single-crystal lattice is amorphized around the periphery of the recess. A layer of amorphous material having the same chemical composition as that of the initial substrate is deposited on the structure obtained. The structure obtained is thermally annealed in order to recrystallize the amorphous material so as to be continuous with the single-crystal lattice of the initial substrate.

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